

NP90N06VDK

60 V – 90 A – N-channel Power MOS FET

Application: Automotive

R07DS1297EJ0100

Rev.1.00

Oct 26, 2015

Description

NP90N06VDK is N-channel MOS Field Effect Transistor designed for high current switching applications.

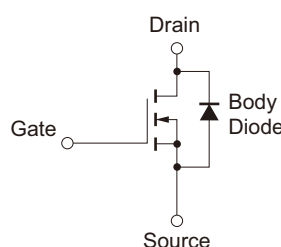
Features

- Super low on-state resistance
— $R_{DS(on)1} = 5.3 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 10 \text{ V}$, $I_D = 45 \text{ A}$)
- Low C_{iss} : $C_{iss} = 4000 \text{ pF TYP.}$ ($V_{DS} = 25 \text{ V}$)
- Designed for automotive application and AEC-Q101 qualified

Outline



TO-252(MP-3ZP)



Equivalent circuit

Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Ordering Information

Part No.	Lead Plating	Packing		Package
NP90N06VDK-E1-AY *1	Pure Sn (Tin)	Tape 2500 p/reel	Taping (E1 type)	TO-252(MP-3ZP)
NP90N06VDK-E2-AY *1			Taping (E2 type)	

Note: *1. Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0\text{ V}$)	V_{DSS}	60	V
Gate to Source Voltage ($V_{DS} = 0\text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 90	A
Drain Current (pulse) ^{*1}	$I_{D(pulse)}$	± 360	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	147	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	1.2	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +175	$^\circ\text{C}$
Repetitive Avalanche Current ^{*2}	I_{AR}	33	A
Repetitive Avalanche Energy ^{*2}	E_{AR}	108	mJ

Notes: ^{*1}. $T_C = 25^\circ\text{C}$, $PW \leq 10\text{ }\mu\text{s}$, Duty Cycle $\leq 1\%$

^{*2}. $R_G = 25\text{ }\Omega$, $V_{GS} = 20\text{ V} \rightarrow 0\text{ V}$

Thermal Resistance

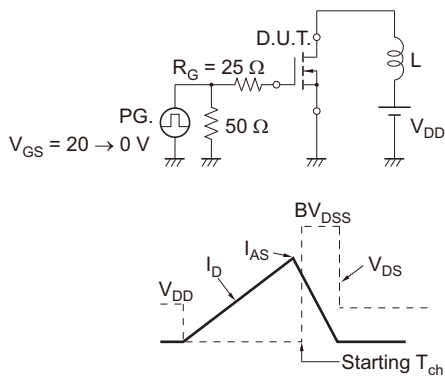
Channel to Case Thermal Resistance	$R_{th(ch-C)}$	1.02	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	125	$^\circ\text{C/W}$

Electrical Characteristics (T_A = 25°C)

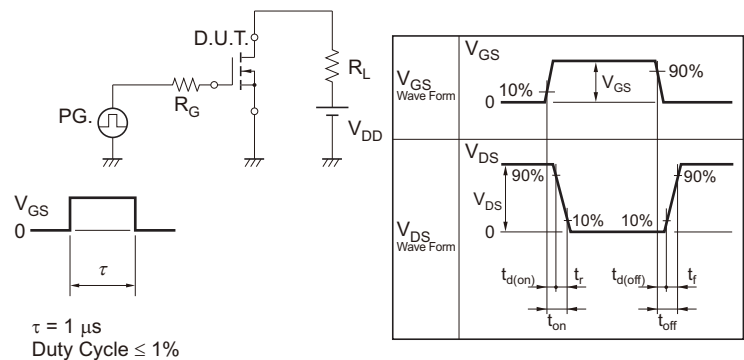
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 60 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±100	nA	V _{GS} = ±20 V, V _{DS} = 0 V
Gate to Source Threshold Voltage	V _{GS(th)}	1.5	2.1	2.5	V	V _{DS} = V _{GS} , I _D = 250 μA
Forward Transfer Admittance *1	y _{fs}	40	80		S	V _{DS} = 5 V, I _D = 45 A
Drain to Source On-state Resistance *1	R _{DS(on)1}		3.8	5.3	mΩ	V _{GS} = 10 V, I _D = 45 A
	R _{DS(on)2}		4.9	8.2	mΩ	V _{GS} = 4.5 V, I _D = 23 A
Input Capacitance	C _{iss}		4000	6000	pF	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz
Output Capacitance	C _{oss}		360	540	pF	
Reverse Transfer Capacitance	C _{rss}		110	200	pF	
Turn-on Delay Time	t _{d(on)}		24	60	ns	V _{DD} = 30 V, I _D = 45 A, V _{GS} = 10 V, R _G = 0 Ω
Rise Time	t _r		7	20	ns	
Turn-off Delay Time	t _{d(off)}		60	120	ns	
Fall Time	t _f		6	20	ns	
Total Gate Charge	Q _G		63	95	nC	V _{DD} = 48 V, V _{GS} = 10 V, I _D = 90 A
Gate to Source Charge	Q _{GS}		15		nC	
Gate to Drain Charge	Q _{GD}		12		nC	
Body Diode Forward Voltage *1	V _{F(S-D)}		0.9	1.5	V	I _F = 90 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		40		ns	I _F = 90 A, V _{GS} = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q _{rr}		45		nC	

Note: *1. Pulsed test

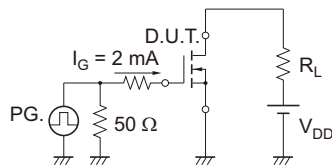
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

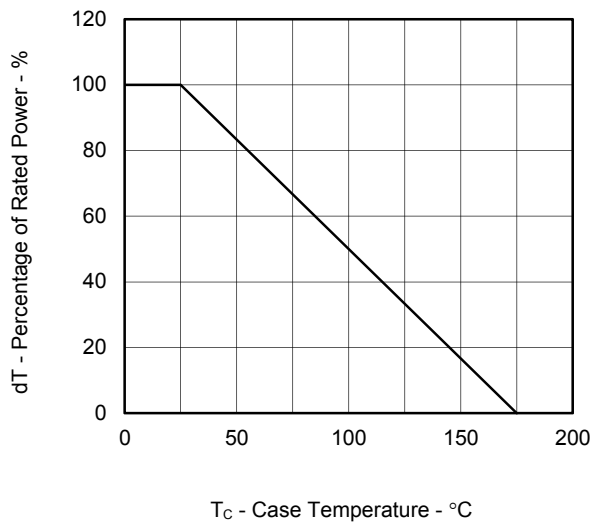


TEST CIRCUIT 3 GATE CHARGE

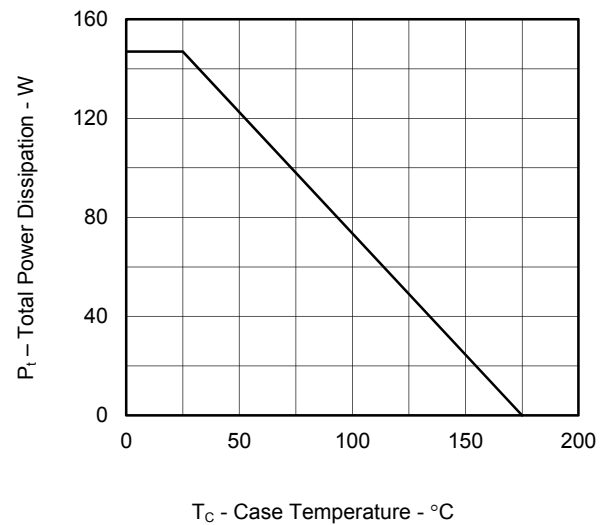


Typical Characteristics ($T_A = 25^\circ\text{C}$)

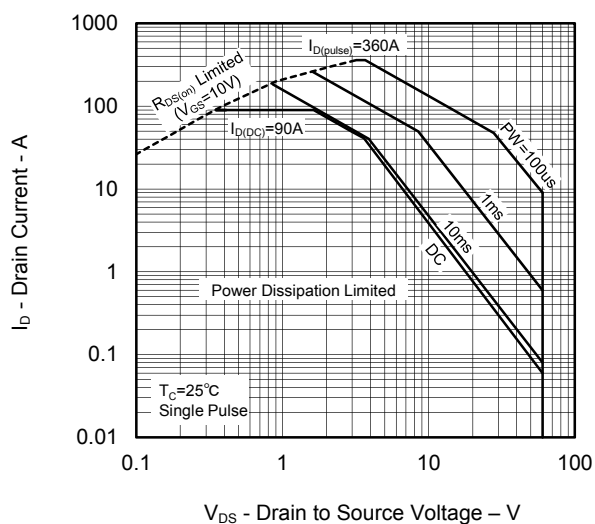
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



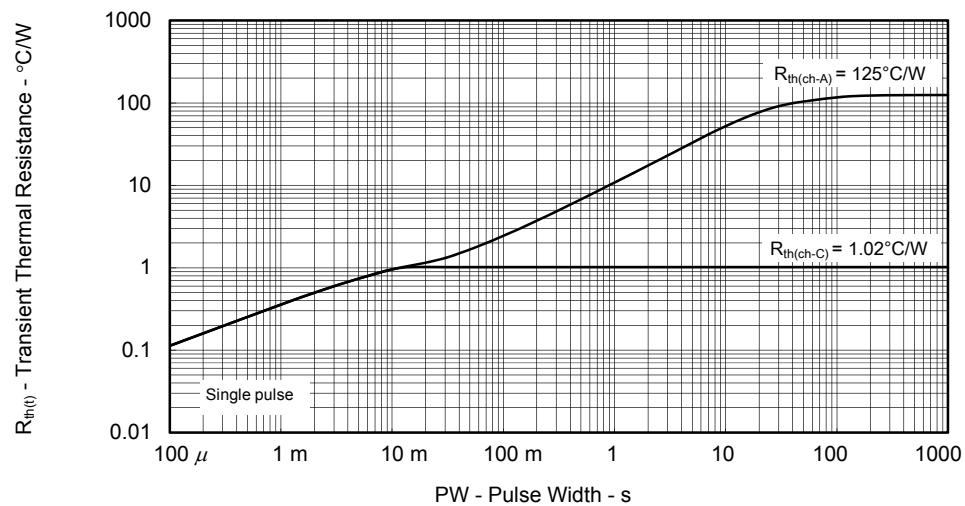
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

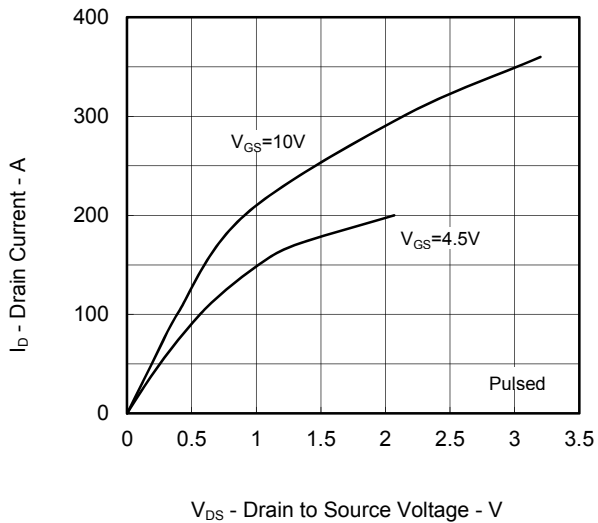


FORWARD BIAS SAFE OPERATING AREA

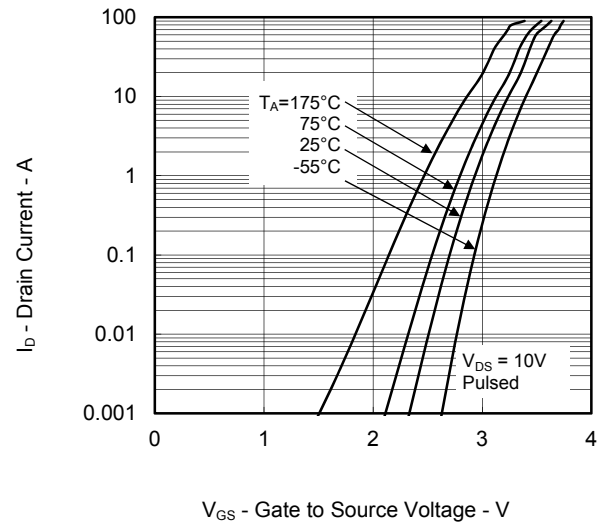
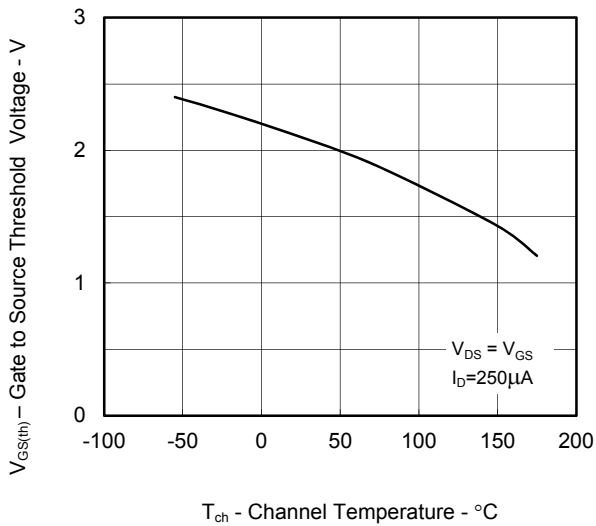
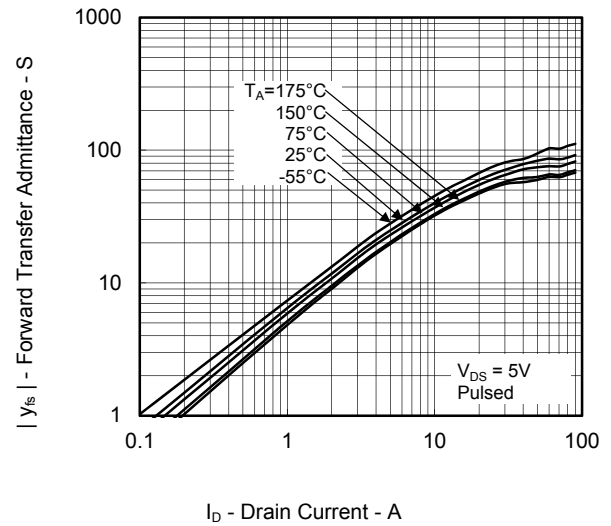
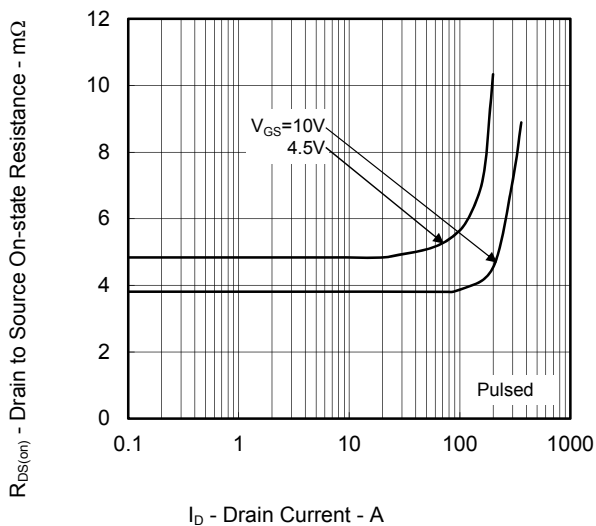
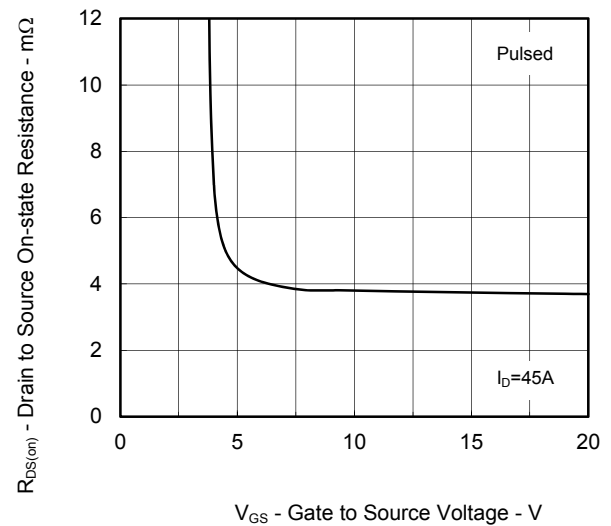


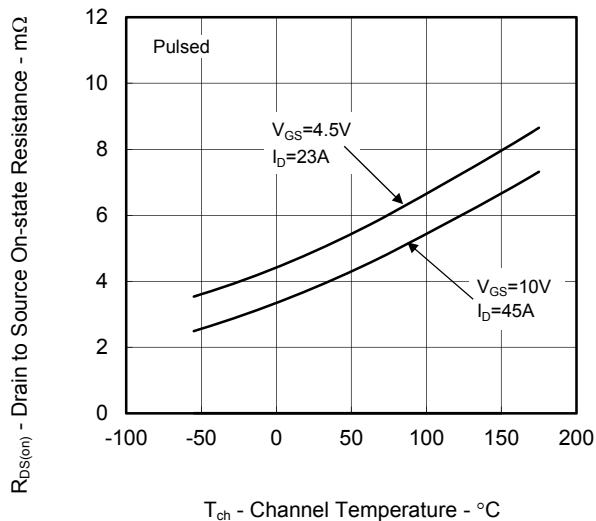
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



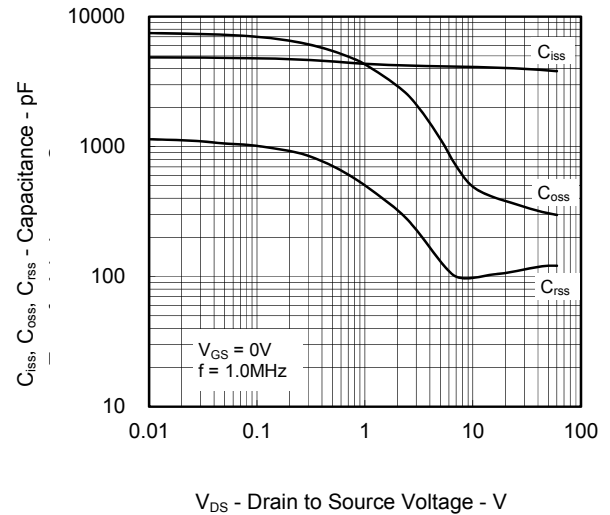
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

FORWARD TRANSFER CHARACTERISTICS

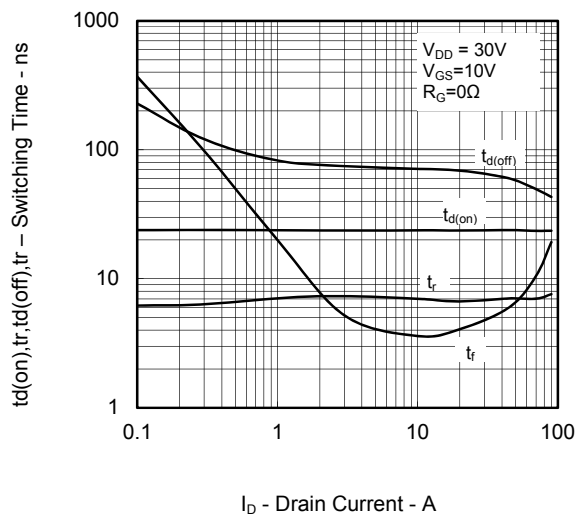
GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATUREFORWARD TRANSFER ADMITTANCE vs. DRAIN
CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE

DRAIN TO SOURCE ON-STATE RESISTANCE vs.
CHANNEL TEMPERATURE

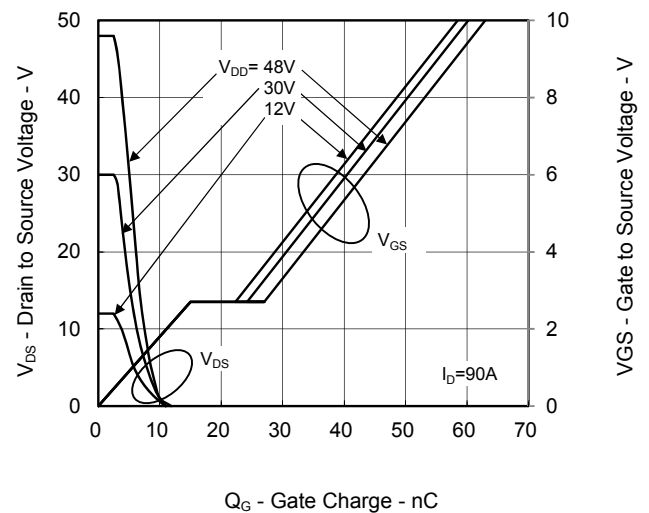
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



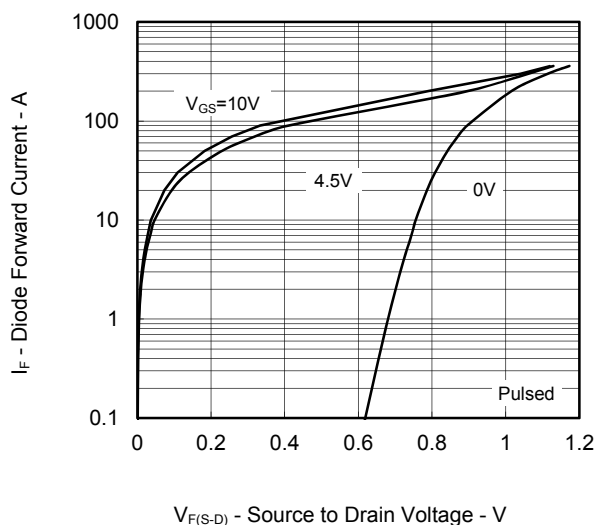
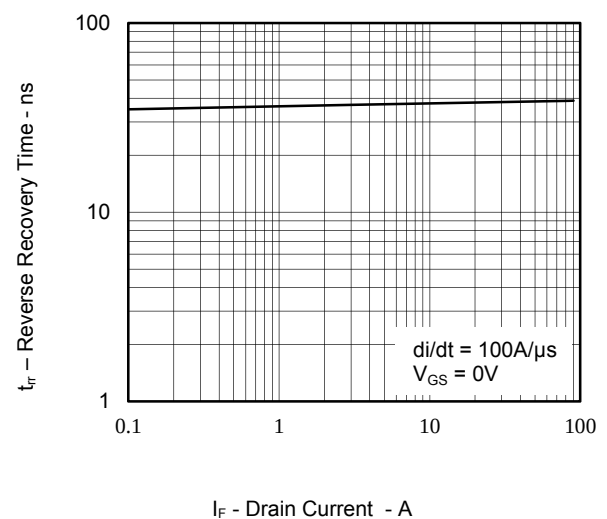
SWITCHING CHARACTERISTICS



DYNAMIC INPUT CHARACTERISTICS

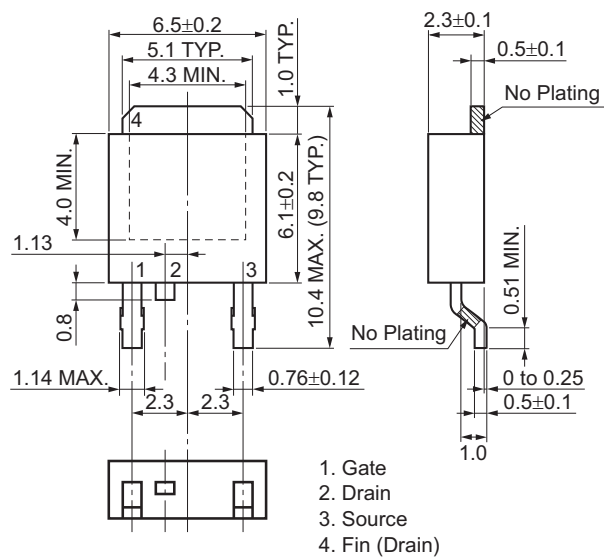


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

REVERSE RECOVERY TIME vs.
DRAIN CURRENT

Package Drawings (Unit: mm)**TO-252 (MP-3ZP) (Mass: 0.3 g TYP.)**

Renesas package code: PRSS0004ZP-A



Revision History	NP90N06VDK Data Sheet
-------------------------	------------------------------

Rev.	Date	Description	
		Page	Summary
1.00	Oct. 26, 2015	—	First Edition Issued

All trademarks and registered trademarks are the property of their respective owners.

Notice

1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation of these circuits, software, and information in the design of your equipment. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from the use of these circuits, software, or information.
2. Renesas Electronics has used reasonable care in preparing the information included in this document, but Renesas Electronics does not warrant that such information is error free. Renesas Electronics assumes no liability whatsoever for any damages incurred by you resulting from errors in or omissions from the information included herein.
3. Renesas Electronics does not assume any liability for infringement of patents, copyrights, or other intellectual property rights of third parties by or arising from the use of Renesas Electronics products or technical information described in this document. No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
4. You should not alter, modify, copy, or otherwise misappropriate any Renesas Electronics product, whether in whole or in part. Renesas Electronics assumes no responsibility for any losses incurred by you or third parties arising from such alteration, modification, copy or otherwise misappropriation of Renesas Electronics product.
5. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The recommended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.
"Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; and industrial robots etc.
"High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control systems; anti-disaster systems; anti-crime systems; and safety equipment etc.
Renesas Electronics products are neither intended nor authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems, surgical implantations etc.), or may cause serious property damages (nuclear reactor control systems, military equipment etc.). You must check the quality grade of each Renesas Electronics product before using it in a particular application. You may not use any Renesas Electronics product for any application for which it is not intended. Renesas Electronics shall not be in any way liable for any damages or losses incurred by you or third parties arising from the use of any Renesas Electronics product for which the product is not intended by Renesas Electronics.
6. You should use the Renesas Electronics products described in this document within the range specified by Renesas Electronics, especially with respect to the maximum rating, operating supply voltage range, movement power voltage range, heat radiation characteristics, installation and other product characteristics. Renesas Electronics shall have no liability for malfunctions or damages arising out of the use of Renesas Electronics products beyond such specified ranges.
7. Although Renesas Electronics endeavors to improve the quality and reliability of its products, semiconductor products have specific characteristics such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Further, Renesas Electronics products are not subject to radiation resistance design. Please be sure to implement safety measures to guard them against the possibility of physical injury, and injury or damage caused by fire in the event of the failure of a Renesas Electronics product, such as safety design for hardware and software including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult, please evaluate the safety of the final products or systems manufactured by you.
8. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. Please use Renesas Electronics products in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive. Renesas Electronics assumes no liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
9. Renesas Electronics products and technology may not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You should not use Renesas Electronics products or technology described in this document for any purpose relating to military applications or use by the military, including but not limited to the development of weapons of mass destruction. When exporting the Renesas Electronics products or technology described in this document, you should comply with the applicable export control laws and regulations and follow the procedures required by such laws and regulations.
10. It is the responsibility of the buyer or distributor of Renesas Electronics products, who distributes, disposes of, or otherwise places the product with a third party, to notify such third party in advance of the contents and conditions set forth in this document, Renesas Electronics assumes no responsibility for any losses incurred by you or third parties as a result of unauthorized use of Renesas Electronics products.
11. This document may not be reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
12. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products, or if you have any other inquiries.

(Note 1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its majority-owned subsidiaries.

(Note 2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.



SALES OFFICES

Renesas Electronics Corporation

<http://www.renesas.com>

Refer to "<http://www.renesas.com/>" for the latest and detailed information.

Renesas Electronics America Inc.

2801 Scott Boulevard Santa Clara, CA 95050-2549, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited

9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3
Tel: +1-905-237-2004

Renesas Electronics Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K
Tel: +44-1628-585-100, Fax: +44-1628-585-900

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.

Room 1709, Quantum Plaza, No.27 ZhichunLu Haidian District, Beijing 100191, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.

Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai, P. R. China 200333
Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited

Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2265-6688, Fax: +852-2886-9022

Renesas Electronics Taiwan Co., Ltd.

13F., No. 363, Fu Shing North Road, Taipei 10543, Taiwan
Tel: +886-2-8175-9600, Fax: +886-2-8175-9670

Renesas Electronics Singapore Pte. Ltd.

80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre, Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.

Unit 1207, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jin Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-9390, Fax: +60-3-7955-9510

Renesas Electronics India Pvt. Ltd.

No.777C, 100 Feet Road, HALII Stage, Indiranagar, Bangalore, India
Tel: +91-80-67208700, Fax: +91-80-67208777

Renesas Electronics Korea Co., Ltd.

12F., 234 Teheran-ro, Gangnam-Gu, Seoul, 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141